

MOSFETs Silicon N-Channel MOS

# SSM3K7002KFU

#### 1. Applications

· High-Speed Switching

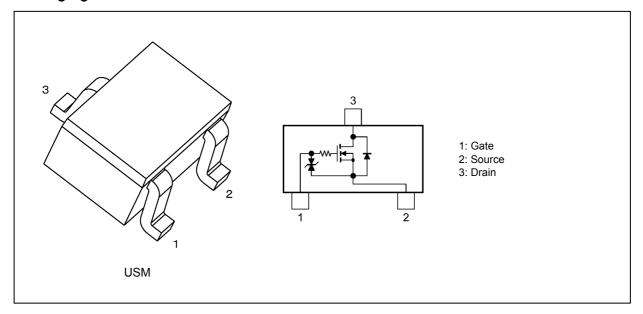
## 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) Low drain-source on-resistance
  - :  $R_{DS(ON)} = 1.05 \Omega \text{ (typ.) } (@V_{GS} = 10 \text{ V})$

 $R_{\rm DS(ON)} = 1.15~\Omega~{\rm (typ.)}~(@V_{\rm GS} = 5.0~{\rm V})$ 

 $R_{\mathrm{DS(ON)}} = 1.2~\Omega~\mathrm{(typ.)}~(@V_{\mathrm{GS}} = 4.5~\mathrm{V})$ 

#### 3. Packaging and Internal Circuit



## 4. Orderable part number

Orderable part number	AEC-Q101		Note	
SSM3K7002KFU,LF	_		General Use	
SSM3K7002KFU,LXG	YES	(Note 1)	Unintended Use	(Note 1)
SSM3K7002KFU,LXH	YES		Automotive Use	

Note 1: For more information, please contact our sales or use the inquiry form on our website.

Start of commercial production

2016-01



## 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	60	V
Gate-source voltage		$V_{GSS}$	±20	
Drain current (DC)	(Note 1)	$I_D$	400	mA
Drain current (pulsed)	(Note 1), (Note 2)	$I_{DP}$	1200	
Power dissipation	(Note 3)	$P_D$	150	mW
Power dissipation	(Note 4)		700	
Channel temperature		$T_ch$	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: pulse width  $\leq$  10  $\mu$ s, Duty  $\leq$  1 %
- Note 3: Device mounted on a 25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm FR4 glass epoxy board (Cu pad: 0.6 mm<sup>2</sup>  $\times$  3)
- Note 4: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

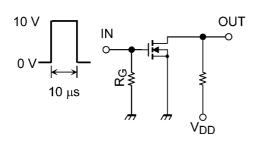
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 16 \text{ V}$	-	_	±10	μА
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V		_	1	
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	$I_D = 250 \mu A, V_{GS} = 0 V$	60	_		V
Gate threshold voltage		$V_{th}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.1	_	2.1	
Drain-source on-resistance	(Note 1)	R <sub>DS(ON)</sub>	I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 4.5 V	_	1.2	1.75	Ω
			I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 5.0 V	_	1.15	1.65	
			I <sub>D</sub> = 100 mA, V <sub>GS</sub> = 10 V	_	1.05	1.5	
Forward transfer admittance	(Note 1)	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 200 mA	_	1	_	S

Note 1: Pulse measurement.

## 6.2. Dynamic Characteristics (Unless otherwise specified, T<sub>a</sub> = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$	_	26	40	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	1.3	_	
Output capacitance	C <sub>oss</sub>		_	5.5	_	
Switching time (rise time)	t <sub>r</sub>	$V_{DD}$ = 30 V, $I_{D}$ = 200 mA,	_	3.6	_	ns
Switching time (turn-on delay time)	t <sub>d(on)</sub>	$V_{GS}$ = 0 to 10 V, R <sub>G</sub> = 50 Ω Duty ≤ 1 %,V <sub>IN</sub> : t <sub>f</sub> , t <sub>f</sub> < 5 ns,	_	5.5	11	
Switching time (fall time)	t <sub>f</sub>	Common source	_	17	_	
Switching time (turn-off delay time)	t <sub>d(off)</sub>		_	38	90	

## 6.3. Switching Time Test Circuit



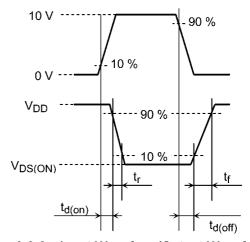


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

## 6.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD}$ = 30 V, $I_{D}$ = 200 mA,	_	0.39	0.6	nC
Gate-source charge	Q <sub>gs</sub>	V <sub>GS</sub> = 4.5 V	_	0.2		
Gate-drain charge	Q <sub>gd</sub>		_	0.11		

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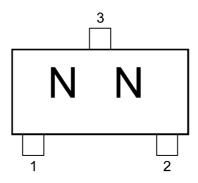


## 6.5. Source-Drain Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	$V_{DSF}$	$I_D = -115 \text{ mA}, V_{GS} = 0 \text{ V}$		-0.79	-1.1	V

Note 1: Pulse measurement.

## 7. Marking





#### 8. Characteristics Curves (Note)

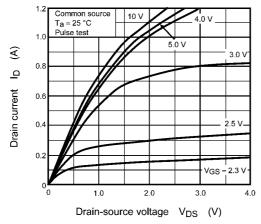


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

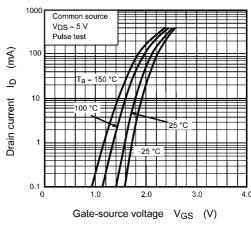


Fig. 8.2 I<sub>D</sub> - V<sub>GS</sub>

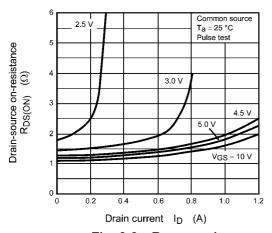


Fig. 8.3 R<sub>DS(ON)</sub> - I<sub>D</sub>

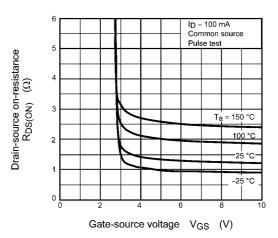


Fig. 8.4 R<sub>DS(ON)</sub> - V<sub>GS</sub>

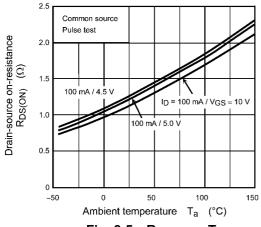


Fig. 8.5  $R_{DS(ON)}$  -  $T_a$ 

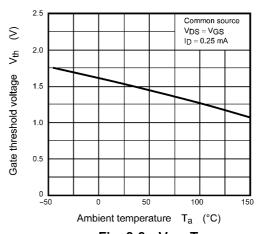
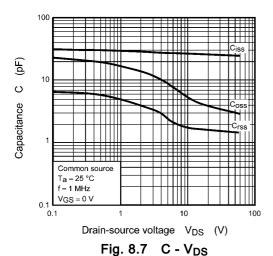
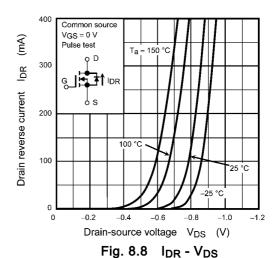
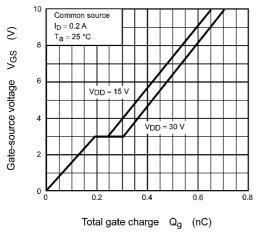


Fig. 8.6 V<sub>th</sub> - T<sub>a</sub>









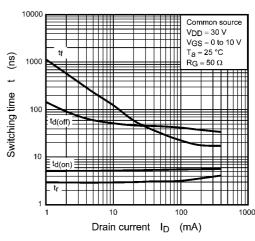
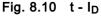
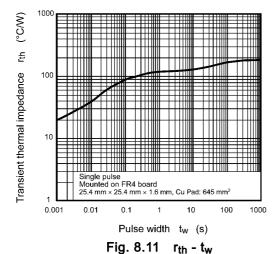


Fig. 8.9 Dynamic Input Characteristics





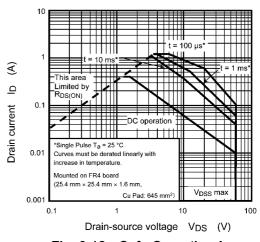


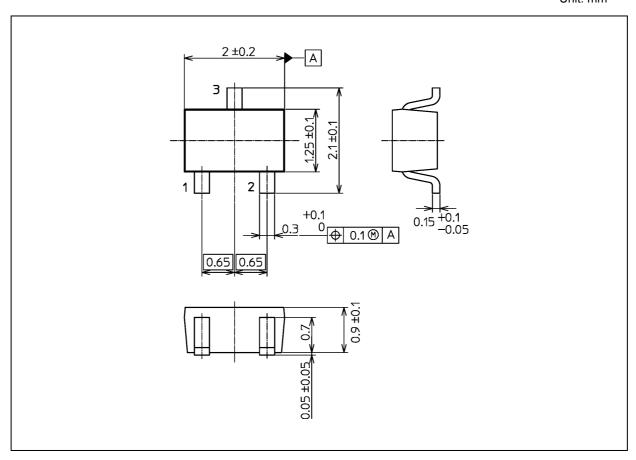
Fig. 8.12 Safe Operating Area

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 6.0 mg (typ.)

	Package Name(s)
TOSHIBA: 2-2E1S	
Nickname: USM	



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